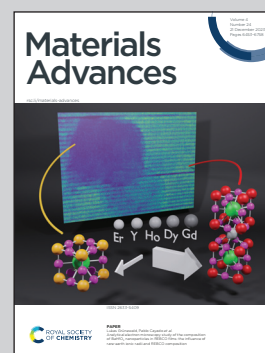


Showcasing research from Professor Hui Sun's laboratory, School of Space Science and Physics, Shandong University, Weihai, China.

Amorphous N-doped InSnZnO thin films deposited by RF sputtering for thin-film transistor application

N-doped InSnZnO thin-film transistors were prepared using radio frequency magnetron sputtering at room temperature. The influence of RF power on the films' microstructure and optical properties was investigated. The results show that an appropriate RF power can enhance ITZO:N film's quality, and reduce the interface state density, which is beneficial to improving the carrier concentration of ITZO:N TFT. Then, the device's performance can be optimized.

As featured in:



See Wanxia Wang, Hui Sun *et al.*, *Mater. Adv.*, 2023, 4, 6535.